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Altri autori (Persone)	BrillsonL. J
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Nota di contenuto	""Preface""; ""Contributors""; ""Contents""; ""1 Ohmic Contacts to GaAs and Other III-V Compounds: Correlation of Microstructure with Electrical Properties""; ""2 Stable and Epitaxial Contacts to III-V Compound Semiconductors""; ""3 Schottky Barriers and Ohmic Contacts to Silicon""; ""4 Insulator/Semiconductor Contacts""; ""5 Interface States""; ""6 Atomic Structure of Metal/GaAs Interfaces: The Role of Defects, Epitaxy, and Morphology""; ""7 Atomic-Scale Chemistry of Metal-Semiconductor Interfaces"" ""8 Survey of Recent Developments in the Theoretical Description of the Properties of Semiconductor Interfaces""""9 Atomic-Scale Control of Heterojunction Band Lineups""; ""Index""
Sommario/riassunto	The authors present the state of the art in growing, processing, and characterizing electronic junctions. Overall, they have assembled a broad array of the latest semiconductor interface science and technology, ranging from advanced ohmic, Schottky, and heterojunction contacts to the refined perspectives of microscopic junctions gleaned from ultrahigh vacuum surface science techniques. Considerable progress has been made in these areas over the last few years. This book is intended for technologists and solid state researchers alike.

